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INTEGRATED CIRCUITS, SILICON MONOLITHIC BIPOLAR OPERATIONAL AMPLIFIERS BASED ON TYPE LM 101A

ESCC Detail Specification No. 9101/001

ISSUE 1 October 2002



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INTEGRATED CIRCUITS, SILICON MONOLITHIC

BIPOLAR OPERATIONAL AMPLIFIERS

BASED ON TYPE LM 101A

ESA/SCC Detail Specification No. 9101/001

space components coordination group

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DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.
		This issue supersedes Issue 2 and incorporates all modifications agreed on the basis of Policy DCR 21019 (Appendices to Detail Specifications), DCR 23058 (new Table 2, 3(a), 3(b) and Figure 4 format) and the following DCR's:- P21. Table 2 : AVS, PSRR, CMRR and V _{OUT} tests moved to d.c. parametersP34. Figure 5 : Modification of burn-in circuit	22110 22110
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'В'	Dec. '82	P1. Cover page P2. DCR page P10. Figure 2(a) : Modification of Title	None None 23093
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No. 9101/001

Rev 'D'

DOCUMENTATION CHANGE NOTICE

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'D'	Dec. '91	P1.Cover pageP2A. DCN: Page addedP3.T of C: Para. 4.3.3 deletedP7.Table 1(a): Variant 07 addedP8.Table 1(b): No. 4, Characteristics amended to include Variant 07P9.Figure 1: Note 2 amended to include Variant 07P11.Figure 2(b): Title amended to include Variant 07P15.Para. 4.2.2: Deviation deleted, "None." addedP16.Para. 4.2.5: Deviation deleted, "None." addedPara. 4.3.2: Paragraph amended to include Variant 07Para. 4.3.2: Paragraph amended to include Variant 07Para. 4.3.3: Paragraph amendedPara. 4.5.2: Paragraph amended	None None 22915 22915 22915 22915 21048 22919 22919 22915 22921 22915 22915 22915
		This specification has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.	

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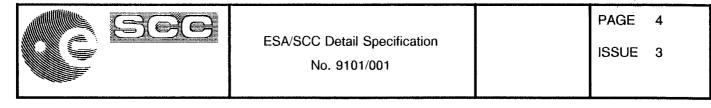
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N/A

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1. <u>GENERAL</u>

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, bipolar operational amplifier, based on Type LM 101A. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

As per Figure 1.

1.5 PHYSICAL DIMENSIONS

As per Figure 2.

- 1.6 <u>PIN ASSIGNMENT</u> As per Figure 3(a).
- 1.7 <u>TRUTH TABLE (FIGURE 3(b))</u> Not applicable.
- 1.8 <u>CIRCUIT SCHEMATIC</u> As per Figure 3(c).
- 1.9 <u>FUNCTIONAL DIAGRAM</u> As per Figure 3(d).



TABLE 1(a) - TYPE VARIANTS

DASH No.	CASE	FIGURE	LEAD FINISH
-01	FLAT	2(a)	D2
-02	FLAT	2(a)	D3 or D4
-03	TO99	2(b)	D2
-04	TO99	2(b)	D3 or D4
-05	DIL	2(c)	D2
-06	DIL	2(c)	D3 or D4
-07	TO99	2(b)	D9

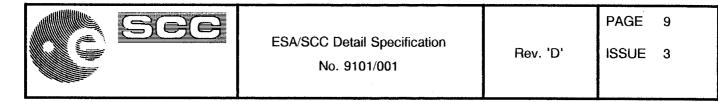


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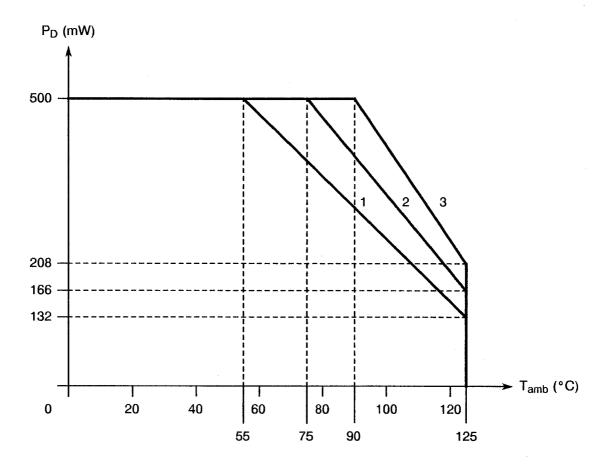
TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNITS	REMARKS
1	Supply Voltage Range	V _S	±22	v	
2	Differential Input Voltage Range	V _{ID}	± 30	V	Note 1
3	Input Voltage Range	VI	± 15	V	Note 2
4	Device Power Dissipation - Type Variants 01-02 - Type Variants 03-04-07 - Type Variants 05-06	PD	500	mW	Note 3 Note 4 Note 5
5	Output Short Circuit Duration	-	Indefinite	mW	Note 6
6	Operating Temperature Range	T _{amb}	- 55 to + 125	°C	
7	Storage Temperature Range	T _{stg}	- 55 to + 150	°C	
8	Soldering Temperature	T _{sol}	+ 300	°C	Note 7
9	Junction Temperature	Tj	+ 150	°C	

- 1. The inputs are shunted with back-to-back diodes for overvoltage protection. Therefore, excessive current will flow if a differential voltage in excess of 1.0V is applied between the inputs, unless some limiting resistance is used.
- 2. If the supply voltage is less than + 15V, the maximum input voltage is equal to the supply voltage.
- 3. Derate above T_{amb} = +55°C at 5.26mW/°C. See Figure 1.
- 4. Derate above T_{amb} = +75°C at 6.67mW/°C. See Figure 1.
- 5. Derate above T_{amb} = +90°C at 8.33mW/°C. See Figure 1.
- 6. Continuous short circuit is allowed for an ambient temperature of +70°C and a case temperature of +125°C.
- 7. Duration: 10 seconds. Distance from case: 1.5mm.







- 1. Derating for type variants 01 and 02.
- 2. Derating for type variants 03, 04 and 07.
- 3. Derating for type variants 05 and 06.

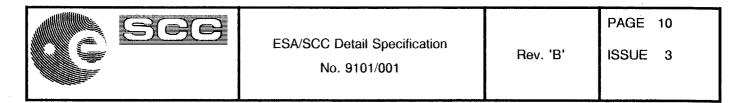
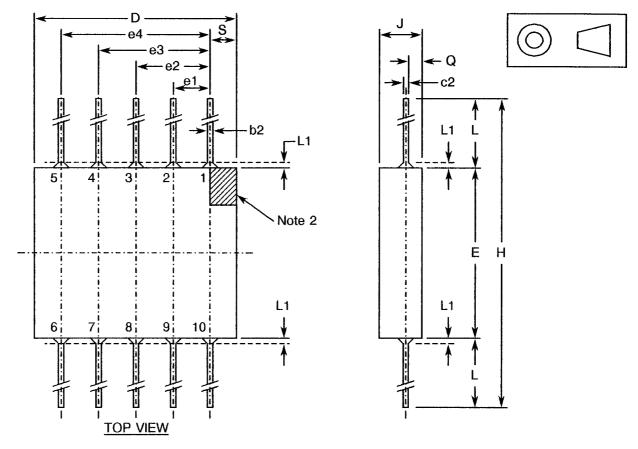


FIGURE 2 - PHYSICAL DIMENSIONS FIGURE 2(a) - VARIANTS 01 AND 02, FLAT PACKAGE TO91



The metric dimensions are calculated from the original dimensions in inches.

SYMBOL	MILLIM	ETRES	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
b2	0.254	0.482	0.010	0.019	
c2	0.077	0.152	0.003	0.006	
D	6.10	6.98	0.240	0.275	
E	6.10	6.60	0.240	0.260	
e1	1.15	1.39	0.045	0.055	1
e2	2.42	2.66	0.095	0.105	1
e3	3.69	3.93	0.145	0.155	1
e4	4.96	5.20	0.195	0.205	1
н	13.72	19.81	0.540	0.780	
J	0.77	1.77	0.030	0.070	
L	3.81	6.60	0.150	0.260	
L1	-	0.38	-	0.015	
Q	0.13	0.83	0.005	0.035	
S	0.52	0.86	0.020	0.035	

- 1. The space between terminals has to be measured at a distance of 0.76mm maximum (0.030 inch) from where the terminals emerge from the case.
- 2. The top face and Pin No. 1 are marked.

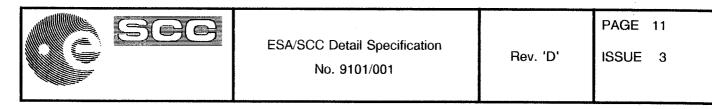
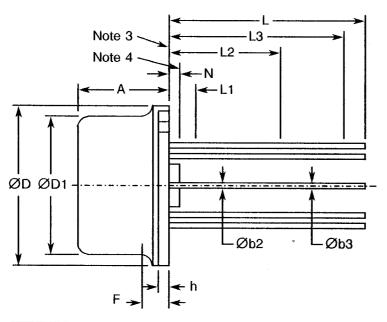
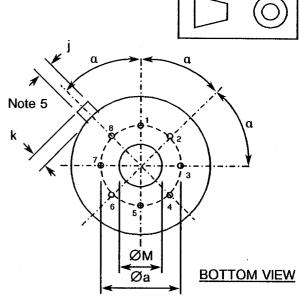


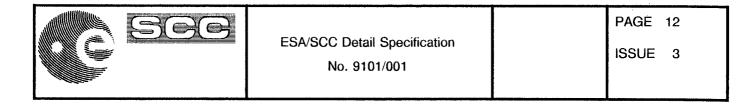
FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED) FIGURE 2(b) - VARIANTS 03, 04 AND 07, METAL CAN TO99

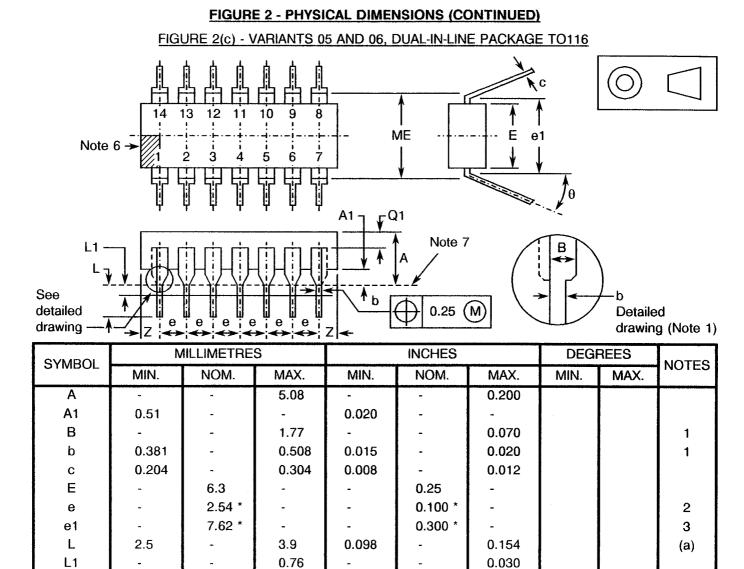




SYMBOL	N	AILLIMETRES	3		INCHES		DEGR.	NOTEO
STMBOL	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	NOM.	NOTES
Øa	-	5.08 (*)	-		0.200 (*)	-		1
A	4.20	-	4.69	0.165	-	0.185		
Øb2	0.407	-	0.508	0.016	-	0.020		
Øb3	-	-	0.53	-	-	0.021		
ØD	8.51	-	9.39	0.335	-	0.370		
ØD1	7.75	-	8.50	0.305	-	0.335		
F	-	-	1.27	-	-	0.050		
h	0.15	-	1.01	0.006	-	0.040		
j	0.712	-	0.863	0.028	-	0.034		
k	0.74	-	1.14	0.029	-	0.045		2
L	12.50	-	14.50	0.492	-	0.071		
L1	-	-	1.27	-	-	0.050		
L2	6.35	-	-	0.250	-	-		
L3	12.70	-	-	0.500	-	-		
ØМ	3.56	-	4.06	0.140	-	0.160		
N	0.26	-	1.01	0.010	-	0.040		
α							45° (*)	1

- 1. The section of each terminal, from a distance of 1.37mm (0.054 inch) to the reference plane, shall be located in a ring whose diameter is 0.99mm (0.039 inch), centred on the accurate geometrical point defining the terminal axis.
- 2. Measured from the D diameter.
- 3. Reference plane.
- 4. Base plane.
- 5. Reference index of Pin 8.
 - * = accurate geometrical location.
 - The metric dimensions are calculated from the original dimensions in inches.





NOTES

ME

Q1

Ζ

θ

n =

1. The lead profile is not required for transition from B to b. The outline of the extreme outputs in the case of F.105A may differ from that of the others, as shown in the Figure.

0.300

0.325

0.080

0

15

3

4

5

- 2. The space between leads is measured on the area L1.
- 3. Measured when the value of the angle $\boldsymbol{\theta}$ is zero.
- 4. Case F.105: Z between e/2 and e (1.27mm<Z<2.54mm). Case F.105A: Z less than e/2 (Z<1.27mm).
- 5. n = quantity of leads.
- 6. Area for visible reference mark on top face.
- 7. Base plane.
- * = accurate geometrical location.

7.62

7×2

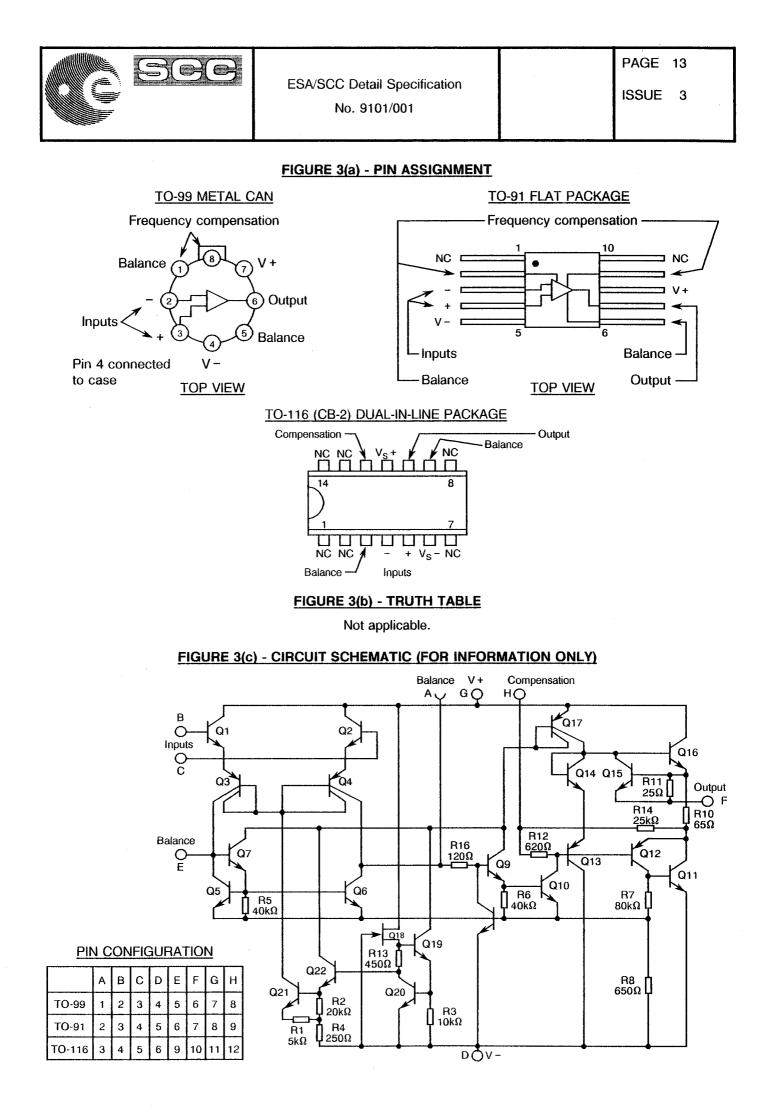
(a) Recommended dimensions for the future: minimum 3.0mm (0.122 inch).

maximum 3.9mm (0.154 inch).

The metric dimensions are calculated from the original dimensions in inches.

8.25

2.03



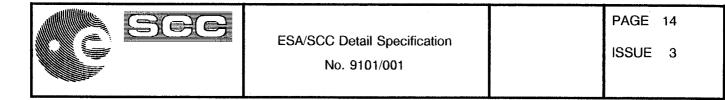
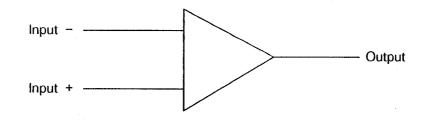


FIGURE 3(d) - FUNCTIONAL DIAGRAM





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2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviations are used:-

- K_{OV} = Overshoot.
- S_{VR} = Supply Voltage Rejection Ratio.
- V_{OM} = Maximum Range of Output Voltage.
- I_{OS} = Output Short Circuit Current.
- I_{CC} = Supply Current.

4. **REQUIREMENTS**

4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein are stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

The following deviations from ESA/SCC Generic Specification No. 9000 shall apply:-

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II) None.



4.2.3 Deviations from Burn-in Tests (Chart III)

Subpara. 7.1.1(a), "High Temperature Reverse Bias" test and subsequent electrical measurements related to this test shall be omitted.

4.2.4 <u>Deviations from Qualification, Environmental and Endurance Tests (Chart IV)</u> None.

4.2.5 <u>Deviations from Lot Acceptance Tests (Chart V)</u> None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be for:-

 Variants 01, 02:
 0.35 grammes.

 Variants 03, 04 and 07:
 1.50 grammes.

 Variants 05, 06:
 2.00 grammes.

4.4 MATERIALS

The materials shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.



4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

The leads shall be Type 'D' with either Type '2', Type '3 or 4' or Type '9' finish in accordance with ESA/SCC Basic Specification No. 23500 (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of components delivered to this specification shall be in accordance with ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

An index shall be located at the top of the package in the position defined in Note 2 of Figure 2 (Variants 01, 02), Note 5 of Figure 2 (Variants 03, 04, 07) or Note 6 of Figure 2 (Variants 05, 06). Alternatively, a tab may be used to identify Pin No. 1. The pin numbering shall be read with the index or tab on the left-hand side.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>910100102B</u>
Detail Specification Number	
Type Variant, as applicable	
Testing Level (B or C, as applicable)	

4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with ESA/SCC Basic Specification No. 21700.



4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL CHARACTERISTICS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at T_{amb} = +22 ± 3 °C.

4.6.2 <u>Electrical Measurements at High and Low Temperatures</u>

The parameters to be measured at high and low temperatures are scheduled in Tables 3(a) and 3(b). The measurements shall be performed at T_{amb} = +125°C and -55°C respectively.

4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.



4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Burn-in

Circuits for use in performing the burn-in tests are shown in Figure 5 of this specification.



ISSUE 3

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TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

	Characteristics	Sumbol	Test Method	Test	Meas'd	Test Conditions	Lin	nits	Unit
No.	Chara cteristics	Symbol	MIL-STD 883	Fig.	Value	Test Conditions	Min	Max	Unit
1	Input Offset Voltage	V _{IO1}	4001	4(a)	E ₁ (V)	$+ V_{CC} = + 20V, - V_{CC} = -20V$ $V_{IN} = 0V$	-	2.0	mV
2	Input Offset Voltage	V _{IO2}	4001	4(a)	E ₂ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	2.0	mV
3	Input Offset Current	l ₁₀₁	4001	4(b)	E ₃ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	10	nA
4	Input Offset Current	I ₁₀₂	4001	4(b)	E ₄ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	10	nA
5	Input (Plus) Bias Current	l +1B1	4001	4(c)	E ₅ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	75	nA
6	Input (Plus) Bias Current	_{+1B2}	4001	4(c)	E ₆ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	75	nA
7	Input (Minus) Bias Current	I _{- IB1}	4001	4(d)	E ₇ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	75	nA
8	Input (Minus) Bias Current	_{-1B2}	4001	4(d)	E ₈ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	75	nA
9	Power Supply Current	I _{CC(-)}	4005	4(e)	lcc	$+V_{CC} = +20V, -V_{CC} = -20V$	-	3.0	mA
10	Short Circuit Output Current (Plus)	I _{OS(+)}	3011	4(f)	los	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = -15V$ Note 1	- 40	- 9.0	mA
11	Short Circuit Output Current (Minus)	I _{OS(-)}	3011	4(f)	los	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	40	mA
12	Open Loop Voltage Gain (Plus)	+ A _{VS}	4004	4(g)	E ₉ (V)	+ V_{CC} = + 20V, - V_{CC} = - 20V V _{IN} = - 15V, R _L = 2.0k	50	-	V/mV
13	Open Loop Voltage Gain (Minus)	- A _{VS}	4004	4(g)	E ₁₀ (V)	+ V_{CC} = + 20V, - V_{CC} = - 20V V _{IN} = + 15V, R _L = 2.0k	50	-	V/mV



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TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

No.	Characteristics	Symbol	Test Method	Test	Meas'd	Test Conditions	Lin	nits	Unit
110.	Characteristics	Symbol	MIL-STD 883	Fig.	Value	Test Conditions	Min	Мах	Unit
14	Open Loop Voltage Gain (Plus)	+ A _{VS}	4004	4(g)	E ₁₁ (V)	+ V _{CC} = +5.0V, - V _{CC} = -5.0V V _{IN} = -2.0V, R _L = 2.0k	10	-	V/mV
15	Open Loop Voltage Gain (Minus)	- A _{VS}	4004	4(g)	E ₁₂ (V)	+ V _{CC} = +5.0V, - V _{CC} = -5.0V V _{IN} = +2.0V, R _L = 2.0k	10	-	V/mV
16	Power Supply Rejection Ratio (Plus)	+ PSRR	4003	4(h)	E ₁₃ (V)	+ V _{CC} = 10V, - V _{CC} = - 20V V _{IN} = 0V	100	-	V/V
17	Power Supply Rejection Ratio (Minus)	- PSRR	4003	4(h)	E ₁₄ (V)	+ V _{CC} = 20V, - V _{CC} = - 10V V _{IN} = 0V	100	-	V/V
18	Common Mode Rejection Ratio	CMRR	4003	4(i)	E ₁₅ (V)	$+ V_{CC} = 35V, - V_{CC} = -5.0V$ $V_{IN} = -15V$	80	-	dB
19					E ₁₆ (V)	+ V_{CC} = 5.0V, - V_{CC} = - 35V V _{IN} = 15V			
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+ $V_{CC} = 20V, -V_{CC} = -20V$ $V_{IN} = -20V, R_L = 2.0k$	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+ V_{CC} = 20V, - V_{CC} = - 20V V_{IN} = + 20V, R _L = 2.0k	-	- 15	V



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

	Characteristics	Pumbal	Test Method	Test Fig.	Test Conditions	Lin	nits	Unit
No.		Symbol	MIL-STD 883		Test Conditions	Min	Max	
22	Slew Rate (Plus)	SR(+)	4002	4(j)	+ $V_{CC} = \pm 20V$ $V_{IN} = -5.0V$ to +5.0V square $R_L = 2.0k$ Note 2	0.3	-	V/µs
23	Slew Rate (Minus)	SR(-)	4002	4(j)	+ $V_{CC} = \pm 20V$ $V_{IN} = -5.0V$ to +5.0V square $R_L = 2.0k$ Note 2	0.3	-	V/µs
24	RiseTime	RT	4002	4(j)	$V_{CC} = \pm 20V, V_{IN} = 50mV$ $R_L = 2.0k$ Note 2	-	800	ns
25	Overshoot	OS	4002	4(j)	V _{CC} = ±20V, V _{IN} =50mV R _L = 2.0k Note 2	-	20	%

- For sampling inspections and end point tests the duration of measurement of I_{OS} shall be 5 seconds minimum. For other tests, this duration may be reduced to be consistent with automatic test procedures provided that the same limits are maintained.
- 2. Sample Test Inspection Level = II, AQL = 2.5%.



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TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0-5) °C

	Observation	Question	Test Method	Test	Meas'd	Test Conditions	Lin	nits	Unit
No.	Characteristics	Symbol	MIL-STD 883	Fig.	Value	Test Conditions	Min	Мах	Unit
1	Input Offset Voltage	V _{IO1}	4001	4(a)	E ₁ (V)	$+ V_{CC} = + 20V, - V_{CC} = -20V$ $V_{IN} = 0V$	-	3.0	mV
2	Input Offset Voltage	V _{IO2}	4001	4(a)	E ₂ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	3.0	mV
3	Input Offset Current	li01	4001	4(b)	E ₃ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	20	nA
4	Input Offset Current	I ₁₀₂	4001	4(b)	E ₄ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	20	nA
5	Input (Plus) Bias Current	l _{+1B1}	4001	4(c)	E ₅ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	100	nA
6	Input (Plus) Bias Current	l +1B2	4001	4(c)	E ₆ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	100	nA
7	Input (Minus) Bias Current	I - 1B1	4001	4(d)	E ₇ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	100	nA
8	Input (Minus) Bias Current	_{- iB2}	4001	4(d)	E ₈ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	100	nA
9	Power Supply Current	ICC(-)	4005	4(e)	lcc	$+V_{CC} = +20V, -V_{CC} = -20V$	-	2.5	mA
10	Short Circuit Output Current (Plus)	l _{OS(+)}	3011	4(f)	los	+ V _{CC} = + 15V, - V _{CC} = - 15V V _{IN} = - 15V Note 1	- 40	- 9.0	mA
11	Short Circuit Output Current (Minus)	I _{OS(-)}	3011	4(f)	los	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	40	mA
12	Open Loop Voltage Gain (Plus)	+ A _{VS}	4004	4(g)	E ₉ (V)	+ V_{CC} = + 20V, - V_{CC} = - 20V V _{IN} = - 15V, R _L = 2.0k	25	-	V/mV
13	Open Loop Voltage Gain (Minus)	- A _{VS}	4004	4(g)	E ₁₀ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ $V_{IN} = +15V, R_L = 2.0k$	25	-	V/mV



TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE, + 125(+0-5) °C (CONT'D)

No.	Characteristics	Sumpole	Test Method MIL-STD 883	Test Fig.	Meas'd Value	Test Conditions	Limits		Unit
						rest conditions	Min	Мах	Unit
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+ $V_{CC} = 20V$, - $V_{CC} = -20V$ $V_{IN} = -20V$, $R_L = 2.0k$	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+ V_{CC} = 20V, - V_{CC} = - 20V V_{IN} = + 20V, R_L = 2.0k	-	- 15	V



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TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, - 55(+5-0) °C

	Oberreateristics	Cuerch al	Test Method	Test	Meas'd	Test Conditions	Lin	nits	Unit
No.	Characteristics	Symbol	MIL-STD 883	Fig.	Value	Test Conditions	Min	Max	Unit
1	Input Offset Voltage	V _{IO1}	4001	4(a)	E ₁ (V)	$+ V_{CC} = + 20V, - V_{CC} = -20V$ $V_{IN} = 0V$	-	3.0	mV
2	Input Offset Voltage	V _{IO2}	4001	4(a)	E ₂ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ $V_{IN} = 0V$	-	3.0	mV
3	Input Offset Current	l _{iO1}	4001	4(b)	E ₃ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	20	nA -
4	Input Offset Current	I ₁₀₂	4001	4(b)	E ₄ (V)	+ V_{CC} = +5.0V, - V_{CC} = -5.0V R _S = 100k, V _{IN} = 0V	-	20	nA
5	Input (Plus) Bias Current	l _{+ IB1}	4001	4(c)	E ₅ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	100	nA
6	Input (Plus) Bias Current	I _{+ IB2}	4001	4(c)	E ₆ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	100	nA
7	Input (Minus) Bias Current	_{-1B1}	4001	4(d)	E ₇ (V)	$+V_{CC} = +20V, -V_{CC} = -20V$ R _S = 100k, V _{IN} = 0V	-	100	nA
8	Input (Minus) Bias Current	I _{- IB2}	4001	4(d)	E ₈ (V)	$+V_{CC} = +5.0V, -V_{CC} = -5.0V$ R _S = 100k, V _{IN} = 0V	-	100	nA
9	Power Supply Current	ICC(-)	4005	4(e)	lcc	$+V_{CC} = +20V, -V_{CC} = -20V$	-	3.75	mA
10	Short Circuit Output Current (Plus)	I _{OS(+)}	3011	4(f)	l _{OS}	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = -15V$ Note 1	- 55	- 9.0	mA
11	Short Circuit Output Current (Minus)	I _{OS(-)}	3011	4(f)	los	$+V_{CC} = +15V, -V_{CC} = -15V$ $V_{IN} = +15V$ Note 1	9.0	55	mA
12	Open Loop Voltage Gain (Plus)	+ A _{VS}	4004	4(g)	E ₉ (V)	+ V_{CC} = + 20V, - V_{CC} = - 20V V _{IN} = - 15V, R _L = 2.0k	25	-	V/mV
13	Open Loop Voltage Gain (Minus)	- A _{VS}	4004	4(g)	E ₁₀ (V)	+ V_{CC} = + 20V, - V_{CC} = - 20V V _{IN} = + 15V, R _L = 2.0k	25	-	V/mV

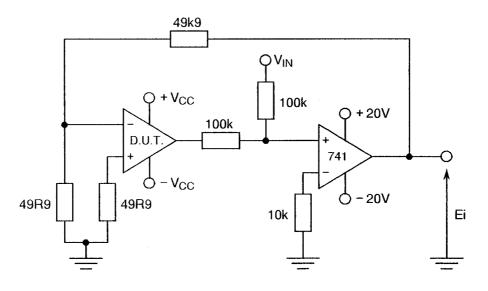


TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE, - 55(+5-0) °C (CONT'D)

No.	Characteristics	Sumpol			Meas'd	Test Conditions	Lin	Unit	
					Value		Min	Max	Unit
20	Output Voltage Swing (Plus)	V _{OUT(+)}	4004	4(g)	E ₁₇ (V)	+ V_{CC} = 20V, - V_{CC} = - 20V V _{IN} = - 20V, R _L = 2.0k	15	-	V
21	Output Voltage Swing (Minus)	V _{OUT(-)}	4004	4(g)	E ₁₈ (V)	+ V_{CC} = 20V, - V_{CC} = - 20V V _{IN} = + 20V, R _L = 2.0k	-	- 15	V



FIGURE 4(a) - INPUT OFFSET VOLTAGE

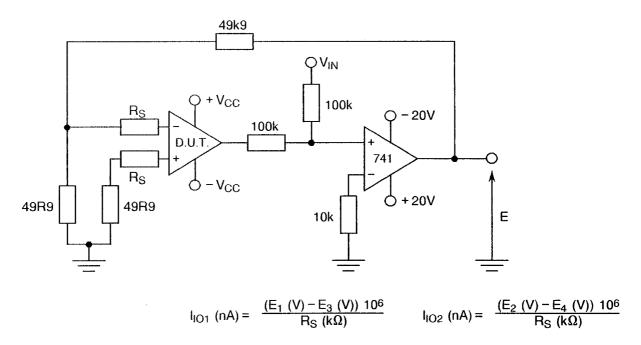


 V_{IO1} (mV) = E_1 (V), V_{IO2} (mV) = E_2 (V).

NOTES

1. All resistors to be 0.1% tolerance.

FIGURE 4(b) - INPUT OFFSET CURRENT

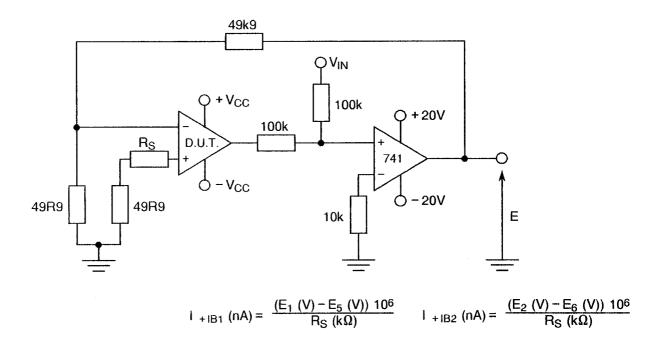


NOTES

1. All resistors to be 0.1% tolerance.



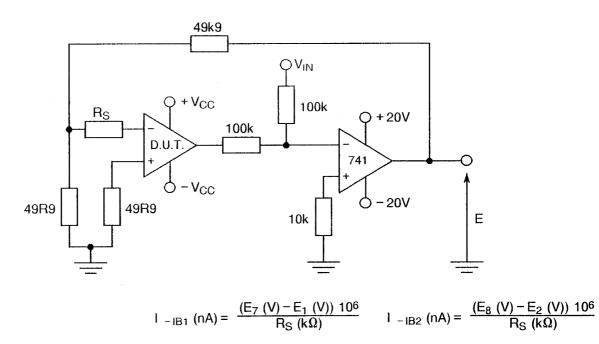
FIGURE 4(c) - INPUT (PLUS) BIAS CURRENT



NOTES

1. All resistors to be 0.1% tolerance.

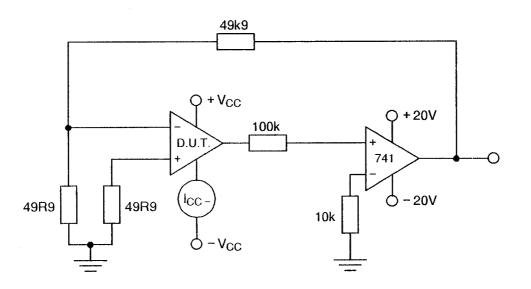
FIGURE 4(d) - INPUT (MINUS) BIAS CURRENT



NOTES 1. All resistors to be 0.1% tolerance.



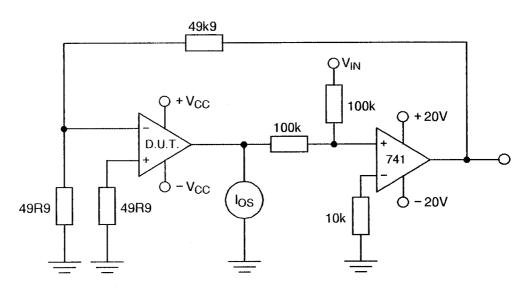
FIGURE 4(e) - SUPPLY CURRENT



NOTES

1. All resistors to be 0.1% tolerance.

FIGURE 4(f) - SHORT CIRCUIT OUTPUT CURRENT

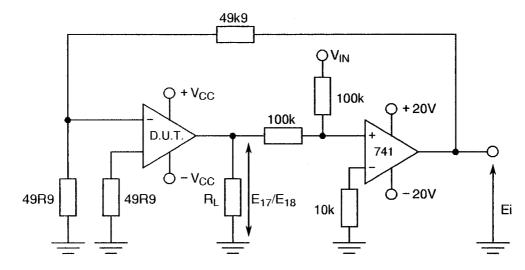


NOTES

1. All resistors to be 0.1% tolerance.



FIGURE 4(g) - OUTPUT VOLTAGE SWING - OPEN LOOP VOLTAGE GAIN

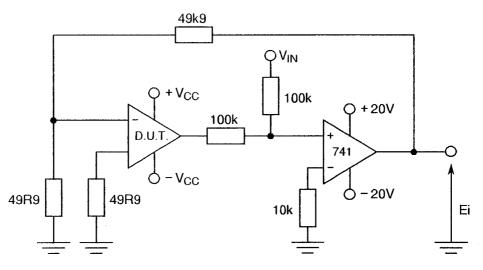


- 1. $V_{OUT} = (E_{17}, E_{18})$
- 2. $+A_{VS} = \frac{15}{E_1 E_9}$, $+A_{VS} = \frac{2}{E_2 E_{11}}$
- 3. $-A_{VS} = \frac{15}{E_{10} E_1}$, $-A_{VS} = \frac{2}{E_{12} E_2}$

NOTES

- 1. E_9 , E_{10} , E_{11} , E_{12} is in Volts.
- 2. All resistors to be 0.1% tolerance.

FIGURE 4(h) - POWER SUPPLY REJECTION RATIO



+ PSRR (μ V/V) = (E₁ (V) - E₁₃ (V)) 10², - PSRR (μ V/V) = (E₁ (V) - E₁₄ (V)) 10²

NOTES

1. Ei is measured to four digits accuracy.

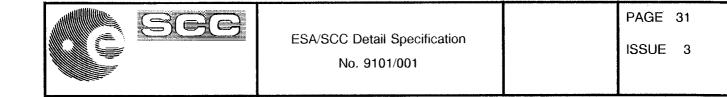
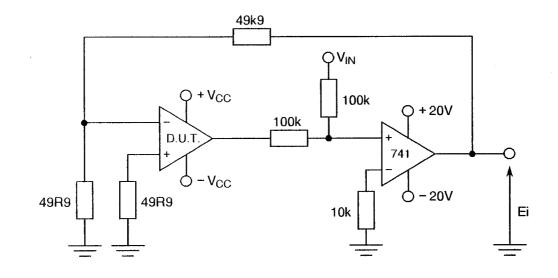


FIGURE 4(i) - COMMON MODE REJECTION RATIO



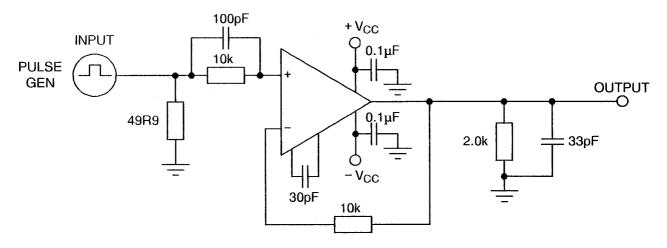
CMRR (dB) = 20 LOG
$$\frac{30.10^3}{E_{15} (V) - E_{16} (V)}$$

NOTES

1. Resistors of $49R9\Omega$ at inputs shall be of 0.01% tolerance matched to 0.001%. Remaining resistors shall be of 0.1% tolerance.



FIGURE 4(k) - DYNAMIC TEST MEASUREMENT CIRCUIT



- 1. Pulse Generator:
 - Rise time ≤ 10ns
 - Repetition rate 1.0kHz (max.)
 - Pulse voltage: -5.0V to +5.0V for slew rate measurement
 - Pulse voltage: 50mV for rise time and overshoot measurement

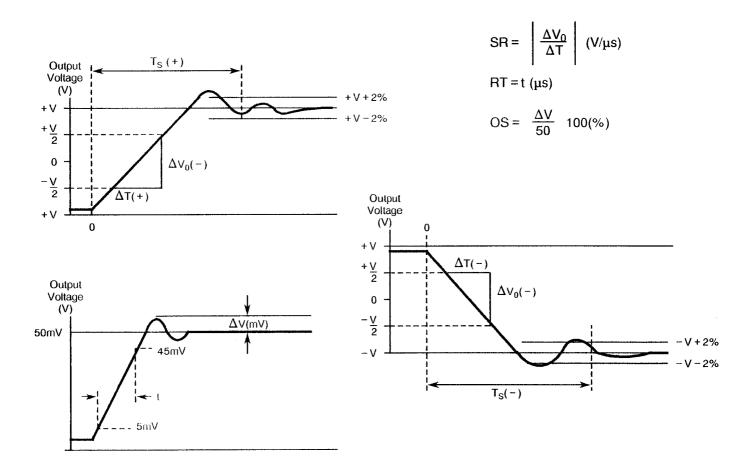




TABLE 4 - PARAMETER DRIFT VALUES

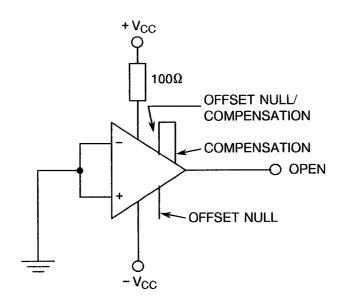
No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
1	Input Offset Voltage Change VIO		As per Table 2	As per Table 2	±0.5	mV
3	Input Offset Current Change	lio	As per Table 2	As per Table 2	± 4.0	nA
5	Input Bias Current Change	I _{IB}	As per Table 2	As per Table 2	± 15	nA

TABLE 5 - CONDITIONS FOR BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1 Ambient Temperature		T _{amb}	+ 125 ± 5	°C
2	Supply Voltage	V _{CC}	±20	V



FIGURE 5 - BURN-IN CIRCUIT





4.8 ENVIRONMENTAL AND ENDURANCE TESTS

4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22 ± 3 °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification.

4.8.3 <u>Electrical Measurements on Completion of Endurance Tests</u>

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.4 Conditions for Operating Life Tests

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 Electrical Circuits for Operating Life Tests

Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be $T_{amb} = +150(+0-5)$ °C.



TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST	LIM	UNIT	
1.0.	UNA KOTENISTICS	STWDOL	TEST METHOD	CONDITIONS	MIN	MAX	
1 -	Input Offset Voltage	V _{IO}	As per Table 2	As per Table 2	-	2.0	mV
3	Input Offset Current	lio	As per Table 2	As per Table 2	-	10	nA
5	Input Bias Current	I _{IB}	As per Table 2	As per Table 2		75	nA
9	Power Supply Current	lcc	As per Table 2	As per Table 2	-	3.0	mA
12	Open Loop Voltage Gain	+ A _{VS}	As per Table 2	As per Table 2	50	-	V/mV



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APPENDIX 'A'

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AGREED DEVIATIONS FOR MOTOROLA (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Table 2 (a.c.)	Tests 22 through to 25: Change V_{CC} condition to $V_{CC} = \pm 18V$.
Tables 2, 3(a) and 3(b)	Tests 3 through to 8: Change R_S condition to $R_S = 10k\Omega$.